



## **Description**

The ACE2341B uses advanced trench technology to provide excellent  $R_{\text{DS(ON)}}$ , low gate charge and operation gate voltages as low as 1.8V. This device is suitable for use as a load switch or other general applications.

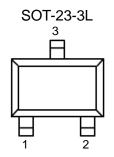
#### **Features**

- VDS=-20V, I<sub>D</sub>=-4.1A
- RDS(ON)<65m $\Omega$  @ V<sub>GS</sub>=-4.5V
- RDS(ON)<85m $\Omega$  @ V<sub>GS</sub>=-2.5V
- RDS(ON)<125m $\Omega$  @ V<sub>GS</sub>=-1.8V

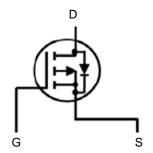
### **Absolute Maximum Ratings**

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Parameter		Symbol	Max	Unit						
Drain-Source Voltage		$V_{DS}$	-20	V						
Gate-Source Voltage		$V_{GS}$	±12	V						
Drain Current (Continuous)	T <sub>A</sub> =25 °C	1_	-4.1	Α						
	T <sub>A</sub> =70 °C	I <sub>D</sub>	-3.2	Α .						
Drain Current (Pulse)		I <sub>DM</sub>	-30	Α						
Power Dissipation	T <sub>A</sub> =25 °C	P <sub>D</sub>	P <sub>D</sub> 1.4							
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to 150	°С						

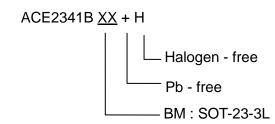
# **Packaging Type**



Description		
Gate		
Source		
Drain		



### **Ordering information**





# **ACE2341B**

### P-Channel Enhancement Mode Field Effect Transistor

### **Electrical Characteristics**

T<sub>A</sub>=25 °C unless otherwise noted

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit			
State									
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}$ =0V, $I_D$ =-250uA	-20			V			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =-16V, $V_{GS}$ =0V			-1	uA			
Gate Leakage Current	I <sub>GSS</sub>	$V_{GS}=\pm 12V$ , $V_{DS}=0V$			±100	nA			
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =-4.5V, $I_{D}$ =-4.3A		55	65	mΩ			
		$V_{GS}$ =-2.5V, $I_{D}$ =-2.5A		70	85				
		$V_{GS}$ =-1.8V, $I_D$ =-2A		112	125				
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250uA$	-0.6	-0.81	-1.4	V			
Forward Transconductance	<b>g</b> <sub>FS</sub>	$V_{DS}$ =-5V, $I_{D}$ =-4A		15		S			
Drain Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.7A,V <sub>GS</sub> =0V		-0.85	-1	V			
Switching									
Total Gate Charge	$Q_g$	V <sub>DS</sub> =-10V, I <sub>D</sub> =-4.5A V <sub>GS</sub> =-4.5V		8.92	11.6	nC			
Gate-Source Charge	$Q_gs$			1.8	2.34				
Gate-Drain Charge	$Q_{gd}$			2.04	2.65				
Turn-On Delay Time	$T_{d(on)}$	$V_{DS}$ =-10V, $R_L$ =10 $\Omega$ $I_D$ =-1A, $R_{GEN}$ =6 $\Omega$ $V_{GS}$ =-4.5V		16.08	32.16				
Turn-On Rise Time	t <sub>f</sub>			5.28	10.56	ns			
Turn-Off Delay Time	$t_{d(off)}$			37.6	75.2				
Turn-Off Fall Time	t <sub>f</sub>			7.28	14.5				
Dynamic									
Input Capacitance	C <sub>iss</sub>	\\		800	960	pF			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =-10V, $V_{GS}$ =0V f=1MHz		131					
Reverse Transfer Capacitance	C <sub>rss</sub>	1-1101112		103					

Note: 1. The value of  $R_{\theta JA}$  is measured with the device mounted on  $1in^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A$ =25°C. The value in any given application depends on the user's specific board design.

- 2. Repetitive rating, pulse width limited by junction temperature.
- 3. The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.





# **Typical Performance Characteristics**

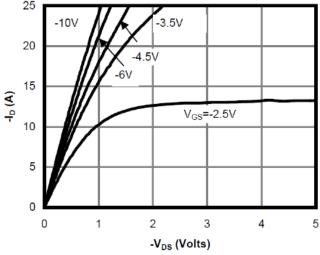


Fig 1: On-Region Characteristics

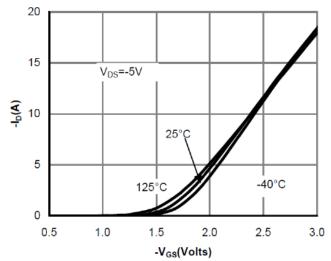


Figure 2: Transfer Characteristics

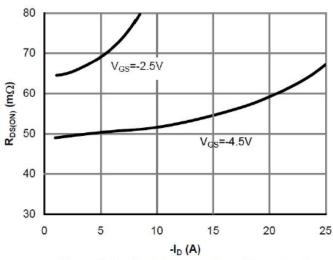


Figure 3: On-Resistance vs. Drain Current and

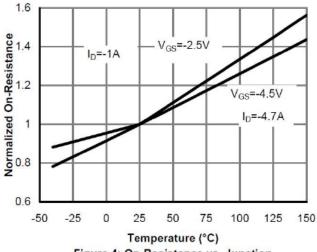


Figure 4: On-Resistance vs. Junction

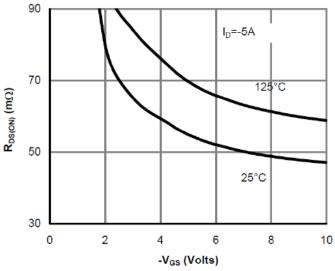


Figure 5: On-Resistance vs. Gate-Source Voltage

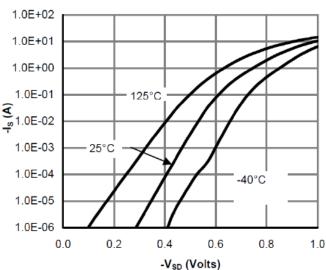


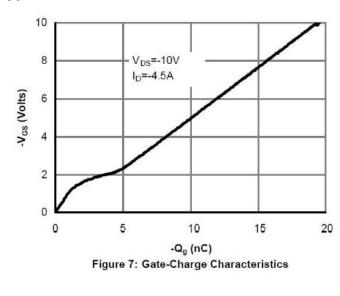
Figure 6: Body-Diode Characteristics

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## **Typical Performance Characteristics**



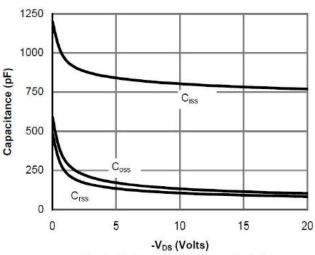
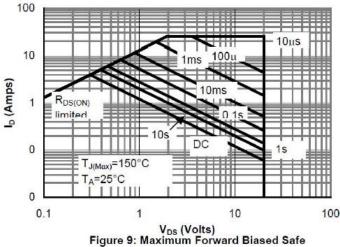


Figure 8: Capacitance Characteristics



**Operating Area** 

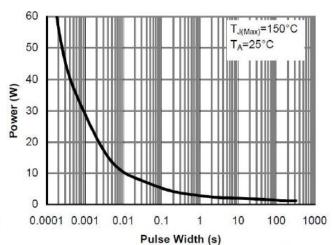


Figure 10: Single Pulse Power Rating Junction-to-**Ambient** 

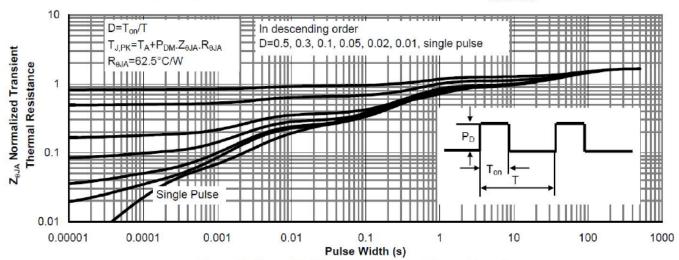
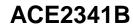


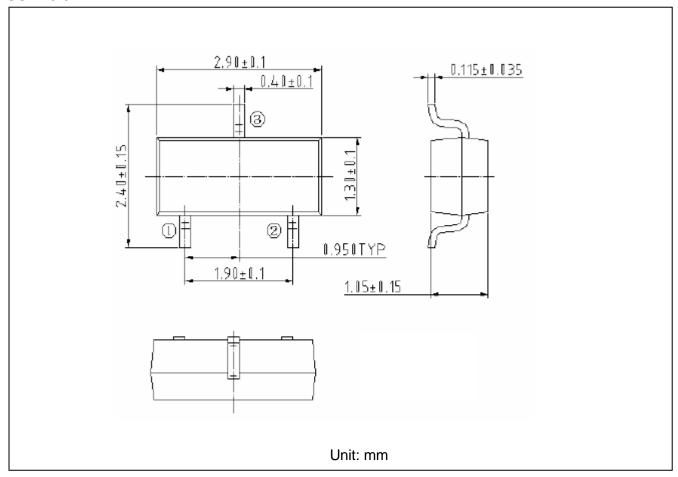
Figure 11: Normalized Maximum Transient Thermal Impedance





# **Packing Information**

## SOT-23-3L





## **ACE2341B**

#### P-Channel Enhancement Mode Field Effect Transistor

#### Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As sued herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and shoes failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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